L Number Hits Search Text 1 1446 high-voltage NEAR circuit\$1	USPAT; US-PGPUB; EPO; JPO;	2002/11/15 12:06
The light veltage (12) at enemies	US-PGPUB;	
	FPU IPU	
	IBM TDB	
COL (I'I also NIDAD singuistit) and transiston	USPAT;	2002/11/15 12:06
2 531 (high-voltage NEAR circuit\$1) and transistor	1	2002/11/15 12.00
	US-PGPUB;	
	EPO; JPO;	
	IBM_TDB	
3 256 ((high-voltage NEAR circuit\$1) and transistor) and ((input output) NEAI		2002/11/15 12:07
terminal\$)	US-PGPUB;	
,	EPO; JPO;	
	IBM_TDB	1
4 239 (((high-voltage NEAR circuit\$1) and transistor) and ((input output)	USPAT;	2002/11/15 12:07
NEAR terminal\$)) and (source darin gate)	US-PGPUB;	
	EPO; JPO;	
	IBM TDB	
5 104 ((((high-voltage NEAR circuit\$1) and transistor) and ((input output)	USPAT;	2002/11/15 12:37
NEAR terminal\$)) and (source darin gate)) and ((first second third)	US-PGPUB;	
	EPO; JPO;	į
NEAR voltage)	IBM_TDB	
1107 220/052 - 1-	USPAT;	2002/11/15 12:37
6 1137 330/253.ccls.		2002/11/13 12.37
	US-PGPUB;	
	EPO; JPO;	
	IBM_TDB	2002/11/15 12 26
7 175 330/253.ccls. and (high-voltage (high NEAR voltage))	USPAT;	2002/11/15 13:26
	US-PGPUB;	
	EPO; JPO;	
	IBM_TDB	
8 0 (330/253.ccls. and (high-voltage (high NEAR voltage))) and (source	USPAT;	2002/11/15 12:40
NEAR2 drain NEAR2 gate)	US-PGPUB;	
	EPO; JPO;	
	IBM TDB	
9 57 (330/253.ccls. and (high-voltage (high NEAR voltage))) and (source	USPĀT;	2002/11/15 13:26
NEAR2 drain NEAR2 gate)	US-PGPUB;	
NET THE GRANT SERVE	EPO; JPO;	
	IBM_TDB	
10 172 (330/253.ccls. and (high-voltage (high NEAR voltage))) and amplifier\$1	USPAT;	2002/11/15 13:09
10 172 (330/253.ccls. and (high-voltage (high NEAR voltage))) and amplifier\$1	US-PGPUB;	2002/11/10
	EPO; JPO;	
	IBM_TDB	
(220/252 1 and (Link and All AD and tops))) and	USPAT;	2002/11/15 12:58
11 142 ((330/253.ccls. and (high-voltage (high NEAR voltage))) and	US-PGPUB;	2002/11/13 12.36
amplifier\$1) and terminal\$1		
	EPO; JPO;	
	IBM_TDB	2002/11/15 12:59
12 142 (((330/253.ccls. and (high-voltage (high NEAR voltage))) and	USPAT;	2002/11/15 12:58
amplifier\$1) and terminal\$1) and (input output)	US-PGPUB;	
	EPO; JPO;	
	IBM_TDB	
13 142 (((((330/253.ccls. and (high-voltage (high NEAR voltage)))) and	USPAT;	2002/11/15 12:59
amplifier\$1) and terminal\$1) and (input output)) and voltage\$1	US-PGPUB;	1
	EPO; JPO;	
	IBM_TDB	
2 ((((((330/253.ccls. and (high-voltage (high NEAR voltage))) and	USPAT;	2002/11/15 13:09
amplifier\$1) and terminal\$1) and (input output)) and voltage\$1) and	US-PGPUB;	
(field ADJ transistor)	EPO; JPO;	
	IBM_TDB	
9 330/253.ccls. and (field ADJ transistor)	USPĀT;	2002/11/15 13:05
(1000)	US-PGPUB;	
	EPO; JPO;	
	IBM_TDB	
16 51 330/\$.ccls. and (field ADJ transistor)	USPAT;	2002/11/15 13:05
16 51 330/\$.ccls. and (field ADJ transistor)	US-PGPUB;	2002/11/15 15:05
	EPO; JPO;	
	IBM TDB	
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Search History 11/15/02 1:30:07 PM Page 1 C:\APPS\east\workspaces\default.wsp

17	8645	257/\$.ccls. and amplifier\$1	USPAT;	2002/11/15 13:16
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
18	86	(257/\$.ccls. and amplifier\$1) and (field ADJ transistor)	USPAT;	2002/11/15 13:17
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
19 9	96	257/368.ccls. and amplifier\$1	USPAT;	2002/11/15 13:24
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
20	1	(257/368.ccls. and amplifier\$1) and (field ADJ transistor)	USPAT;	2002/11/15 13:17
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
	90	(257/368.ccls. and amplifier\$1) and transistor\$1	USPAT;	2002/11/15 13:17
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
22	88	(field ADJ transistor) same amplifier\$1	USPAT;	2002/11/15 13:25
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
23	357	(field ADJ transistor) and amplifier\$1	USPAT;	2002/11/15 13:25
			US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
24	137	((field ADJ transistor) and amplifier\$1) and (high-voltage (high NEAR	USPAT;	2002/11/15 13:26
		voltage))	US-PGPUB;	
			EPO; JPO;	
			IBM_TDB	
25	46	(((field ADJ transistor) and amplifier\$1) and (high-voltage (high NEAR	USPAT;	2002/11/15 13:26
		voltage))) and (source NEAR2 drain NEAR2 gate)	US-PGPUB;	
			EPO; JPO;	
			IBM TDB	